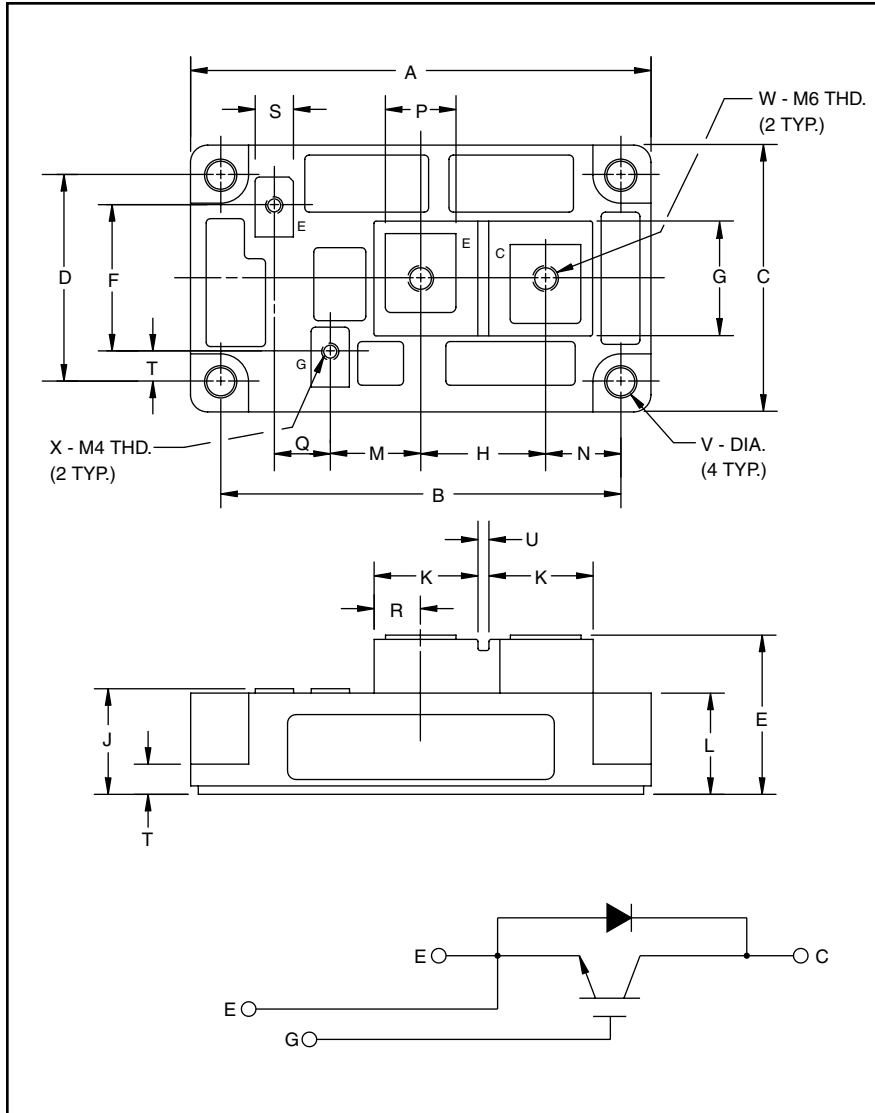


### Single IGBTMOD™ H-Series Module 300 Amperes/1400 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.21	107.0
B	3.661±0.01	93.0±0.25
C	2.44	62.0
D	1.89±0.01	48.0±0.25
E	1.42 Max.	36.0 Max.
F	1.34	34.0
G	1.18	30.0
H	1.14	29.0
J	0.98 Max.	25.0 Max.
K	0.94	24.0
L	0.93	23.5

Dimensions	Inches	Millimeters
M	0.83	21.0
N	0.69	17.5
P	0.63	16.0
Q	0.51	13.0
R	0.43	11.0
S	0.35	9.0
T	0.28	7.0
U	0.12	3.0
V	0.26 Dia.	Dia. 6.5
W	M6 Metric	M6
X	M4 Metric	M4



#### Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of one IGBT Transistor in a single configuration with a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

#### Features:

- Low Drive Power
- Low  $V_{CE(sat)}$
- Discrete Super-Fast Recovery (70ns) Free-Wheel Diode
- High Frequency Operation (20-25kHz)
- Isolated Baseplate for Easy Heat Sinking

#### Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies
- Laser Power Supplies

#### Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM300HA-28H is a 1400V ( $V_{CES}$ ), 300 Ampere Single IGBT-MOD™ Power Module.

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	300	28

**CM300HA-28H**  
**Single IGBTMOD™ H-Series Module**  
 300 Amperes/1400 Volts

**Absolute Maximum Ratings,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified**

Ratings	Symbol	CM300HA-28H	Units
Junction Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	$V_{CES}$	1400	Volts
Gate-Emitter Voltage (C-E SHORT)	$V_{GES}$	$\pm 20$	Volts
Collector Current ( $T_c = 25^\circ\text{C}$ )	$I_C$	300	Amperes
Peak Collector Current ( $T_j \leq 150^\circ\text{C}$ )	$I_{CM}$	600	Amperes
Emitter Current* ( $T_c = 25^\circ\text{C}$ )	$I_E$	300	Amperes
Peak Emitter Current* ( $T_j \leq 150^\circ\text{C}$ )	$I_{EM}$	600	Amperes
Maximum Collector Dissipation ( $T_c = 25^\circ\text{C}$ )	$P_c$	2100	Watts
Max. Mounting Torque M6 Main Terminal Screws	-	26	in-lb
Max. Mounting Torque M6 Mounting Screws	-	26	in-lb
Max. Mounting Torque M4 Terminal Screws	-	13	in-lb
Module Weight (Typical)	-	400	Grams
V Isolation (Main Terminal to Baseplate, AC 1 min.)	$V_{RMS}$	2500	Volts

**Static Electrical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	1.0	mA
Gate Leakage Current	$I_{GES}$	$V_{GE} = V_{CES}, V_{CE} = 0V$	-	-	0.5	$\mu\text{A}$
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 30\text{mA}, V_{CE} = 10V$	5.0	6.5	8.0	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 300\text{A}, V_{GE} = 15V, T_j = 25^\circ\text{C}$	-	3.1	4.2	Volts
		$I_C = 300\text{A}, V_{GE} = 15V, T_j = 125^\circ\text{C}$	-	2.95	-	Volts
Total Gate Charge	$Q_G$	$V_{CC} = 800V, I_C = 300\text{A}, V_{GE} = 15V$	-	1530	-	nC
Emitter-Collector Voltage*	$V_{EC}$	$I_E = 300\text{A}, V_{GE} = 0V$	-	-	3.8	Volts

**Dynamic Electrical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	$C_{ies}$		-	-	60	nF
Output Capacitance	$C_{oes}$	$V_{GE} = 0V, V_{CE} = 10V, f = 1\text{MHz}$	-	-	21	nF
Reverse Transfer Capacitance	$C_{res}$		-	-	12	nF
Resistive	Turn-on Delay Time	$t_{d(on)}$	-	-	250	ns
Load	Rise Time	$t_r$	-	-	500	ns
Switching	Turn-off Delay Time	$t_{d(off)}$	-	-	350	ns
Times	Fall Time	$t_f$	-	-	500	ns
Diode Reverse Recovery Time*	$t_{rr}$	$I_E = 300\text{A}, di_E/dt = -600\text{A}/\mu\text{s}$	-	-	300	ns
Diode Reverse Recovery Charge*	$Q_{rr}$	$I_E = 300\text{A}, di_E/dt = -600\text{A}/\mu\text{s}$	-	3.0	-	$\mu\text{C}$

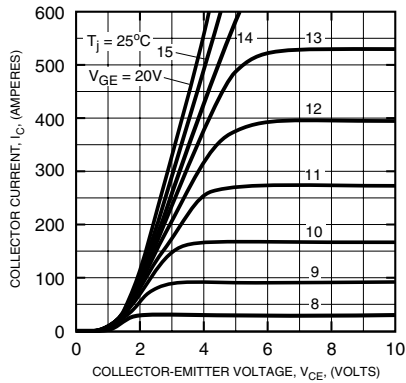
**Thermal and Mechanical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	-	-	0.06	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per FWDi	-	-	0.12	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	-	-	0.04	$^\circ\text{C}/\text{W}$

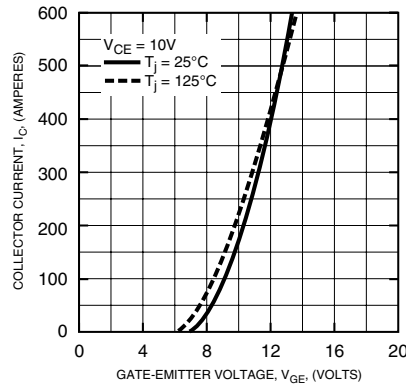
\* Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode.

**CM300HA-28H**  
**Single IGBTMOD™ H-Series Module**  
 300 Amperes/1400 Volts

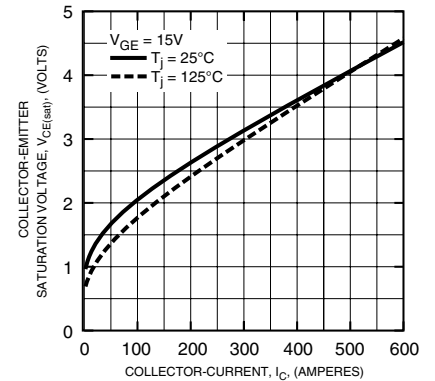
**OUTPUT CHARACTERISTICS (TYPICAL)**



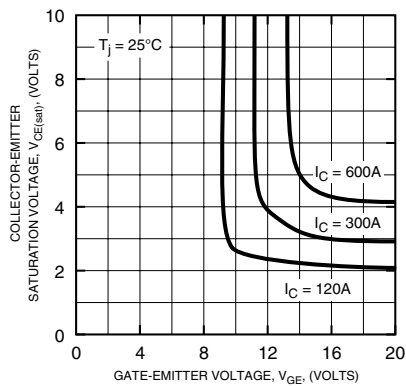
**TRANSFER CHARACTERISTICS (TYPICAL)**



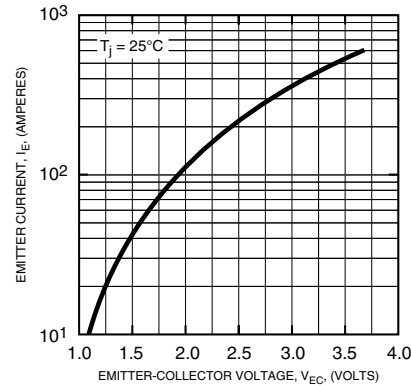
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



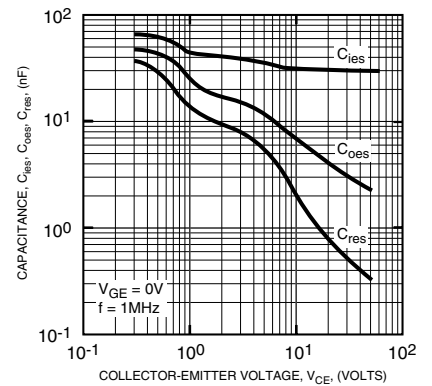
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



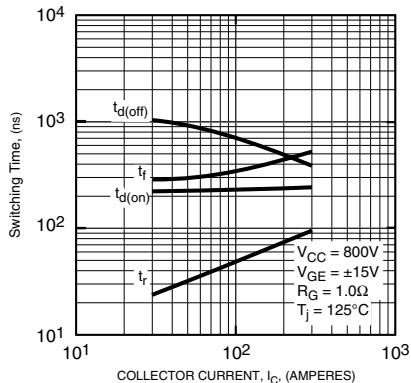
**FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)**



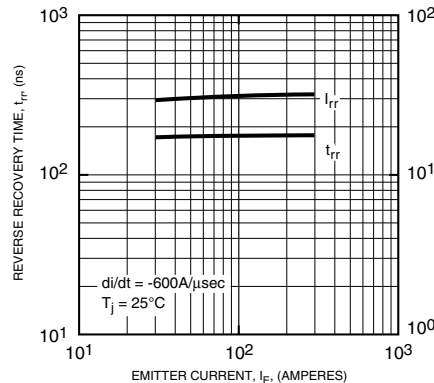
**CAPACITANCE VS. VCE (TYPICAL)**



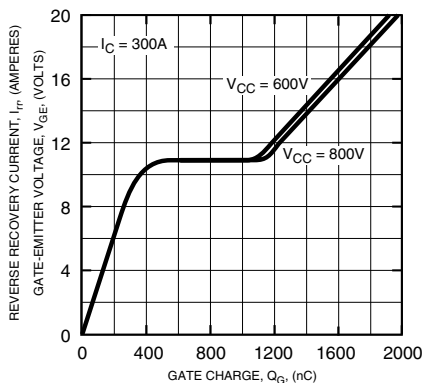
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**



**REVERSE RECOVERY CHARACTERISTICS (TYPICAL)**



**GATE CHARGE, VGE**



**CM300HA-28H**  
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 300 Amperes/1400 Volts

